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XPX403FD

-30V P-Channel Enhancement Mode MOSFET



The XPX403FD uses advanced trench technology to

provide excellent $R_{\text{DS}(\text{ON})},$ low gate charge and

operation with gate voltages as low as 4.5V. This

device is suitable for use as a

Battery protection or in other Switching application.

Application

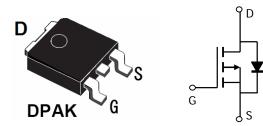
Lithium battery protection

Wireless impact

Mobile phone fast charging



 $V_{DS} = -30V, I_D = -90A$ RDS(ON)=5.0mΩ (typ) @ VGS=-10V RDS(ON)=6.0mΩ (typ) @ VGS=-4.5V



Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)	
XPX403FD	TO-252-3L	XPX403FD XXX YYYY	2500	

Absolute Maximum Ratings (TC=25°Cunless otherwise noted)

Symbol	Parameter	Max.	Units
VDSS	Drain-Source Voltage	-30	V
VGSS	Gate-Source Voltage	±25	V
ID	Continuous Drain Current T_C = 25 $^\circ\!\mathrm{C}$	-100	А
ID	Continuous Drain Current T_C = 100 $^\circ\!\mathrm{C}$	-59	А
IDM	Pulsed Drain Current note1	-280	А
EAS	Single Pulsed Avalanche Energy note2	180	mJ
PD	Power Dissipation $T_C = 25^{\circ}C$	96	W
RθJC	Thermal Resistance, Junction to Case	1.2	°C /W
TJ, TSTG	Operating and Storage Temperature Range -55 to +175		°C



Electrical Characteristics (T_J=25°C, unless otherwise noted)

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
V(BR)DSS	Drain-Source Breakdown Voltage VGS=0V, ID= -250µA		-30	-33	-	V
IDSS	Zero Gate Voltage Drain Current	VDS= -30V, VGS=0V,	-	-	-1	μA
IGSS	Gate to Body Leakage Current	VDS=0V, VGS= ±20V	-	-	±100	nA
VGS(th)	Gate Threshold Voltage	VDS=VGS, ID= -250µA	-1.0	-1.6	-2.5	V
	Static Drain-Source on-Resistance	VGS= -10V, ID= -30A	-	5.0	6.0	mΩ
RDS(on)		VGS= -4.5V, ID= -20A	-	6.0	8.0	
Ciss	Input Capacitance	VDS= -15V, VGS=0V,	-	2890	-	pF
Coss	Output Capacitance			660	-	pF
Crss	Reverse Transfer Capacitance		-	726	-	pF
Qg	Total Gate Charge	VDS= -15V, ID= -30A,	-	30	-	nC
Qgs	Gate-Source Charge			6	-	nC
Qgd	Gate-Drain("Miller") Charge		-	8	-	nC
td(on)	Turn-on Delay Time		-	18	-	ns
tr	Turn-on Rise Time	VDD= -15V, ID= -30A,	-	15	-	ns
td(off)	Turn-off Delay Time	Turn-off Delay Time VGS= -10V, RGEN=2.5Ω		52	-	ns
tf	Turn-off Fall Time		-	21	-	ns
IS	Maximum Continuous Drain to Source DiodeForward Current		-	-	-90	Α
ISM	Maximum Pulsed Drain to Source Diode Forward Current			-	-360	А
VSD	Drain to Source Diode Forward Voltage VGS=0V, IS= -30 A			-0.8	-1.2	V

Notes:

- 1、 Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
- 2 $_{\sim}\,$ E AS condition: T J =25 $^{\circ}\mathrm{C},$ V DD = -15V, V G = -10V, R G =25 $\Omega,$ L=0.5mH, I AS = -29A



Typical Characteristics

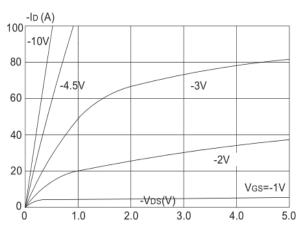


Figure1: Output Characteristics

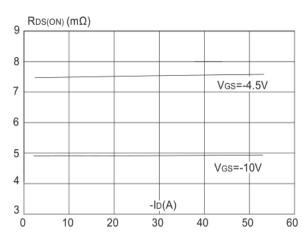
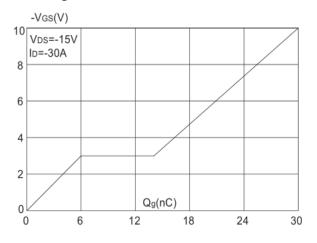


Figure 3:On-resistance vs. Drain Current





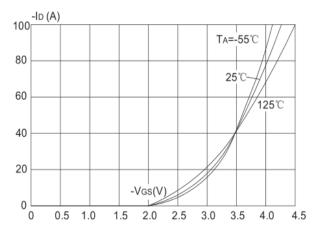
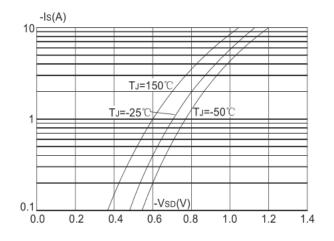


Figure 2: Typical Transfer Characteristics





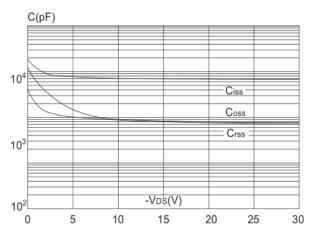
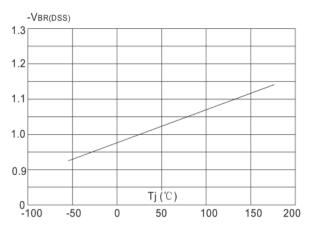
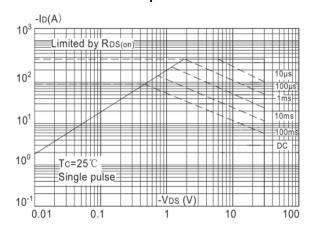


Figure 6: Capacitance Characteristics











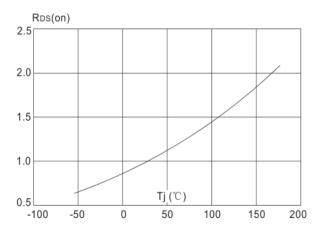


Figure 8: Normalized on Resistance vs.

Junction Temperature

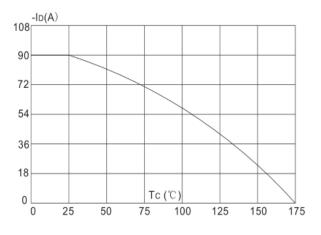


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

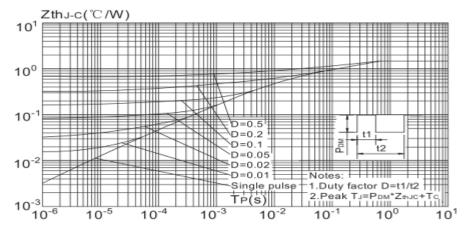
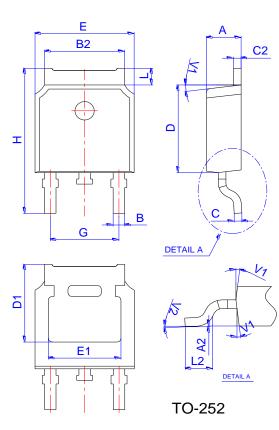


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Case

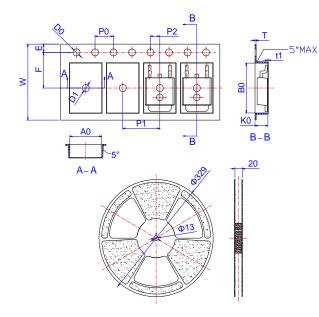


Package Mechanical Data



	Dimensions						
Ref.	Millimeters			Inches			
	Min.	Тур.	Max.	Min.	Тур.	Max.	
A	2.10		2.50	0.083		0.098	
A2	0		0.10	0		0.004	
В	0.66		0.86	0.026		0.034	
B2	5.18		5.48	0.202		0.216	
С	0.40		0.60	0.016		0.024	
C2	0.44		0.58	0.017		0.023	
D	5.90		6.30	0.232		0.248	
D1		5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268	
E1	4.63			0.182			
G	4.47		4.67	0.176		0.184	
Н	9.50		10.70	0.374		0.421	
L	1.09		1.21	0.043		0.048	
L2	1.35		1.65	0.053		0.065	
V1		7°			7°		
V2	0°		6°	0°		6°	

Reel Spectification-TO-252



	Dimensions					
Ref.	Millimeters			Inches		
	Min.	Тур.	Max.	Min.	Тур.	Max.
W	15.90	16.00	16.10	0.626	0.630	0.634
Е	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
D0	1.40	1.50	1.60	0.055	0.059	0.063
D1	1.40	1.50	1.60	0.055	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
A0	6.85	6.90	7.00	0.270	0.271	0.276
B0	10.45	10.50	10.60	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.105	0.109	0.113
Т	0.24		0.27	0.009		0.011
t1	0.10			0.004		
10P0	39.80	40.00	40.20	1.567	1.575	1.583



Flow (wave) soldering (solder dipping)

Product	Peak Temperature	Dipping Time		
Pb device	245℃±5 ℃	5sec±1sec		
Pb-Free device	260 ℃+0/-5℃	5sec±1sec		



This integrated circuit can be damaged by ESD UniverChip Corporation recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedure can cause damage. ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

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